

Part Number: L-93DP3BT

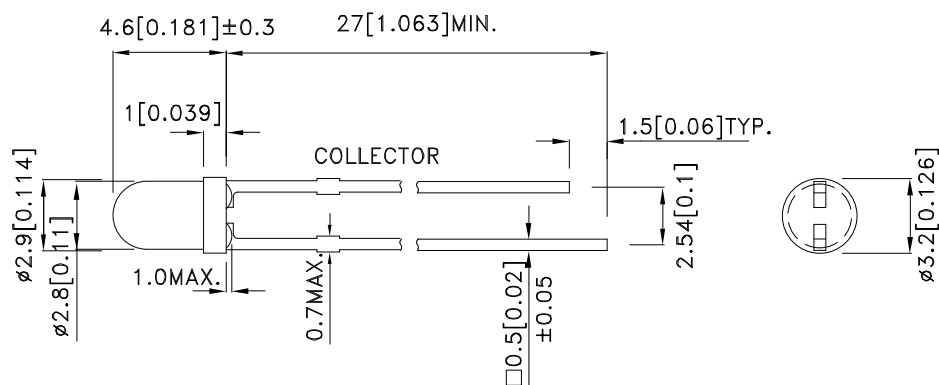
Features

- MECHANICALLY AND SPECTRALLY MATCHED TO THE INFRARED EMITTING LED LAMP.
- BLUE TRANSPARENT LENS.
- RoHS COMPLIANT.

Description

Made with NPN silicon phototransistor chips.

Package Dimensions



Notes:

1. All dimensions are in millimeters (inches).
2. Tolerance is ±0.25(0.01") unless otherwise noted.
3. Lead spacing is measured where the leads emerge from the package.
4. Specifications are subject to change without notice.



Electrical / Optical Characteristics at TA=25°C

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
V _{BR CEO}	Collector-to-Emitter Breakdown Voltage	30			V	I _C =100uA E _e =0mW/c m ²
V _{BR ECO}	Emitter-to-Collector Breakdown Voltage	5			V	I _E =100uA E _e =0mW/c m ²
V _{CE (SAT)}	Collector-to-Emitter Saturation Voltage			0.8	V	I _C =2mA E _e =20mW/c m ²
I _{CEO}	Collector Dark Current			100	nA	V _{CE} =10V E _e =0mW/c m ²
T _R	Rise Time (10% to 90%)		15		us	V _{CE} = 5V I _C =1mA R _L =1000Ω
T _F	Fall Time (90% to 10%)		15		us	
I _(ON)	On State Collector Current	0.07	0.35		mA	V _{CE} = 5V E _e =1mW/c m ² λ=940nm

Absolute Maximum Ratings at TA=25°C

Parameter	Max. Ratings
Collector-to-Emitter Voltage	30V
Emitter-to-Collector Voltage	5V
Power Dissipation at (or below) 25°C Free Air Temperature	100mW
Operating Temperature	-40°C To +85°C
Storage Temperature	-40°C To +85°C
Lead Soldering Temperature (>5mm for 5sec)	260°C